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STATEMENT BY APPLICANT**

### MENT OF THE AIRCRAFT

Sheet 1 of 11

<b>Complete If Known</b>	
Application Number	10/649,712
Filing Date	August 26, 2003
First Named Inventor	Ren, Fan
Art Unit	2812
Examiner Name	
Attorney Docket Number	5853-274

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(Use as many sheets as necessary)

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of 1

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		Kim et al., "Inversion behavior in Sc <sub>2</sub> O <sub>3</sub> /GaN gated diodes," Appl. Phys. Lett., 81: 373-375, July 2002.	
		Simin et al., "7.5kW/mm <sup>2</sup> current switch using AlGaN/GaN metal-oxide-semiconductor heterostructure field effect transistor on SiC substrates," Electronics Letters, 36: November 2000.	
		Mistele et al., "First AlGaN/GaN MOSFET with photoanodic gate dielectric," Materials Science and Engineering, B93, 107-111, 2002.	
		Khan et al., "Enhancement and depletion mode GaN/AlGaN heterostructure field effect transistors," Appl. Phys. Lett., 68: 514-516, January 1996.	
		Simin, et al., "SiO <sub>2</sub> /AlGaN/InGaN/GaN MOSDHFETs," IEEE Electron Device Letters, 23: 458-460, August 2002.	
		Kim et al., "Characteristics of MgO/GaN gate-controlled metal-oxide-semiconductor diodes," Applied Physics Letter, 80: 4555-4557, June 2002.	
		Koudymov et al., "Maximum current in nitride-based heterostructure field-effect transistors," Applied Physics Letters, 80: 3216-3218, April 2002.	
		Hu et al., "Si <sub>3</sub> N <sub>4</sub> /AlGaN/GaN-metal-insulator-semiconductor heterostructure field-effect transistors," Applied Physics Letters, 79: 2832-2834, October 2001.	
		Teles et al., "Spinodal decomposition in B <sub>x</sub> Ga <sub>1-x</sub> N and B <sub>x</sub> Al <sub>1-x</sub> N alloys," Applied Physics Letters, 80: 1177-1179, February 2002.	
		Chou et al., AlGaN/GaN Metal Oxide-Semiconductor Heterostructure Field-Effect Transistor Based on a Liquid Phase Deposited Oxide," Jpn. J. Appl. Phys. 41: L748-L750, July 2002.	

Examiner Signature	<i>W. Pecht</i>	Date Considered	3/05
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